

### KSP5179

# High Frequency Transistor



### 1. Emitter 2. Base 3. Collector

### NPN Epitaxial Silicon Transistor

### Absolute Maximum Ratings T<sub>a</sub>=25°C unless otherwise noted

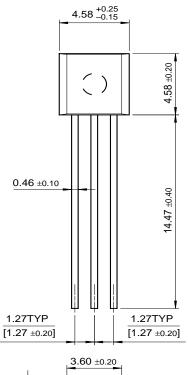
Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	20	V
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	2.5	V
I <sub>C</sub>	Collector Current	50	mA
P <sub>C</sub>	Collector Power Dissipation (T <sub>a</sub> =25°C)	200	mW
	Derate above 25°C	1.6	mW/°C
P <sub>C</sub>	Collector Power Dissipation (T <sub>C</sub> =25°C)	300	mW
	Derate above 25°C	2.4	mW/°C
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

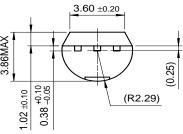
### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

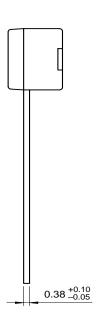
Symbol	Parameter	Test Condition	Min.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =3mA, I <sub>B</sub> =0	12		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =10μA, I <sub>E</sub> =0	20	-10	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	2.5	0.075	V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =15V, I <sub>E</sub> =0 V <sub>CB</sub> =15V, I <sub>E</sub> =0, Ta=150°C	MA	0.02 1	μΑ μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CB</sub> =1V, I <sub>C</sub> =3mA	25	250	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.4	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =6V, I <sub>C</sub> =5mA	900	2000	MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1 to1 MHz		1	pF
h <sub>fe</sub>	Small Signal Current Gain	V <sub>CE</sub> =6V, I <sub>C</sub> =2mA, f=1KHz	25	300	
C <sub>c · rbb</sub> ,	Collector Base Time Constant	V <sub>CE</sub> =6V, I <sub>E</sub> =2mA, f=31.9MHz	3	14	ps
NF	Noise Figure	$V_{CE}$ =6V, $I_{C}$ =1.5mA, f=200MHz $R_{S}$ =50 $\Omega$		4.5	dB

## **Package Dimensions**

TO-92







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
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Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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